Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.7)	V_{pp}	3	kV

ELECTRICAL CHARACTERISTICS (T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	V_D =12V R_L =33	- -	MAX.	5	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	V_D =V_{DRM} T_j =125 R_L =3.3k	- -	MIN.	0.2	V
I_L	I_G =1.2I_{GT}	-	MAX.	15	mA
				20	
I_H	I_T =500mA		MAX.	15	mA
dV/dt	V_D=540V Gate Open T_j =125		MIN.	240	V s
(dI/dt)c	(dV/dt)c=1 9 V_j=1 25		MIN.	1.5	A/ms A/ms

TET 10.7 (L)]TJ 0 scn /C2_0 1 Tf 0 Tc 0 Tw 1.827 0 Td <03C6>Tj /TT4 1 Tf -0.007 Tc 0.007 Tw 1.013 0 Td .1+T 13.7 (86)]TJ 0 Tc 0 Tw 1

FIG.1: Maximum power dissipation versus RMS on-state current

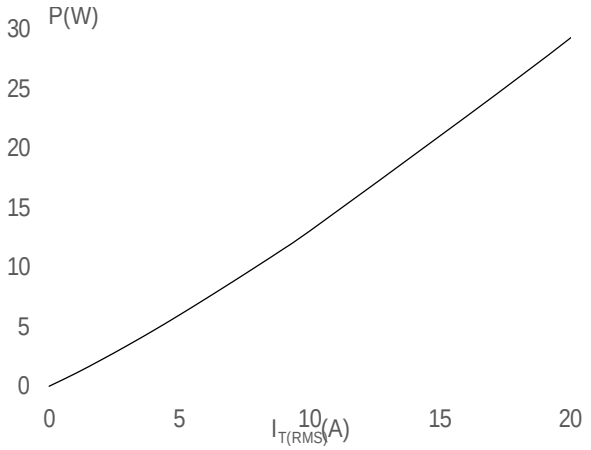


FIG.2: RMS on-state current versus case temperature

JST16C-800TW

ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		- -			
JST16C-800TW	800	5	TO-220C	50	Tube

Document Revision History

Date	Revision	Changes
Apr.12, 2023	A.1.0	Last updated
Oct.15, 2025	A.1.1	Revise PACKAGE MECHANICAL DATA
Sept.16, 2026	A.1.2	Revise I_{TSM}, dV/dt

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